

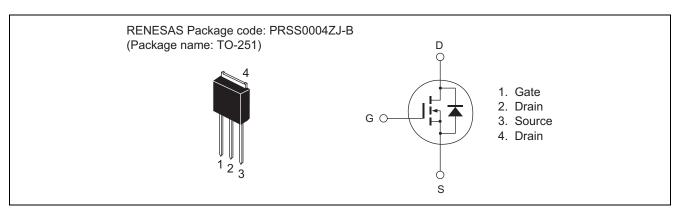
RJK6032DPH-E0

600V - 3A - MOS FET High Speed Power Switching R07DS0993EJ0100 Rev.1.00 Jan 23, 2013

Features

- Low on-resistance $R_{DS(on)}=3.3~\Omega~typ.~(at~I_D=1.0~A,~V_{GS}=10~V,~Ta=25^{\circ}C)$
- Low drive current
- High density mounting

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	600	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I _D	3	Α
Drain peak current	I _{D (pulse)} Note1	6	Α
Body-drain diode reverse drain current	I _{DR}	3	Α
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	6	Α
Avalanche current	I _{AP} Note2	3	Α
Avalanche energy	E _{AR} Note2	0.49	mJ
Channel dissipation	Pch Note3	40.3	W
Channel to case thermal impedance	θch-c	3.1	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. STch = 25° C, Tch $\leq 150^{\circ}$ C
- 3. Value at Tc = 25°C

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

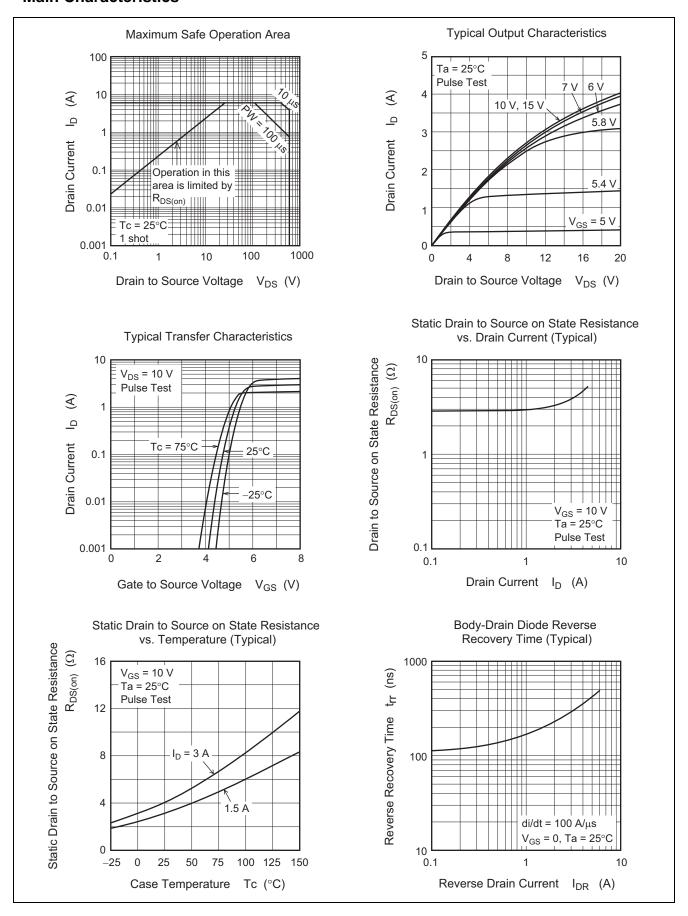
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}			1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}		_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.5	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	3.3	4.3	Ω	$I_D = 1.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	285	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	31	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	3.5	_	pF	
Turn-on delay time	t _{d(on)}	_	13	_	ns	$\begin{split} I_D &= 1.5 \text{ A} \\ V_{GS} &= 10 \text{ V} \\ R_L &= 200 \Omega \\ Rg &= 10 \Omega \end{split}$
Rise time	t _r	_	13	_	ns	
Turn-off delay time	t _{d(off)}	_	22	_	ns	
Fall time	t _f	_	22	_	ns	
Total gate charge	Qg	_	9.0	_	nC	$V_{DD} = 480 \text{ V}$ $V_{GS} = 10 \text{ V}$ $I_D = 3 \text{ A}$
Gate to source charge	Qgs	_	1.7	_	nC	
Gate to drain charge	Qgd	_	4.9	_	nC	
Body-drain diode forward voltage	V_{DF}	_	0.9	1.5	V	$I_F = 3 A$, $V_{GS} = 0$ Note4
Body-drain diode reverse recovery time	t _{rr}		300	_	ns	$I_F = 3 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

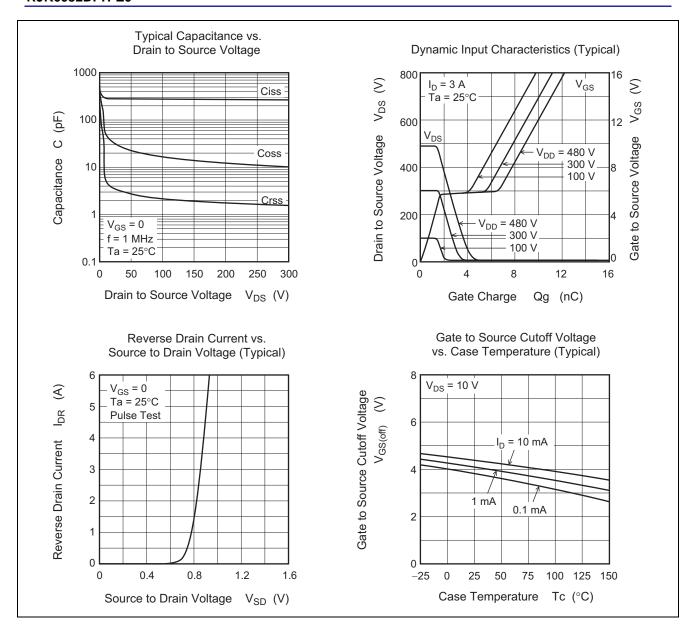
Notes: 4. Pulse test

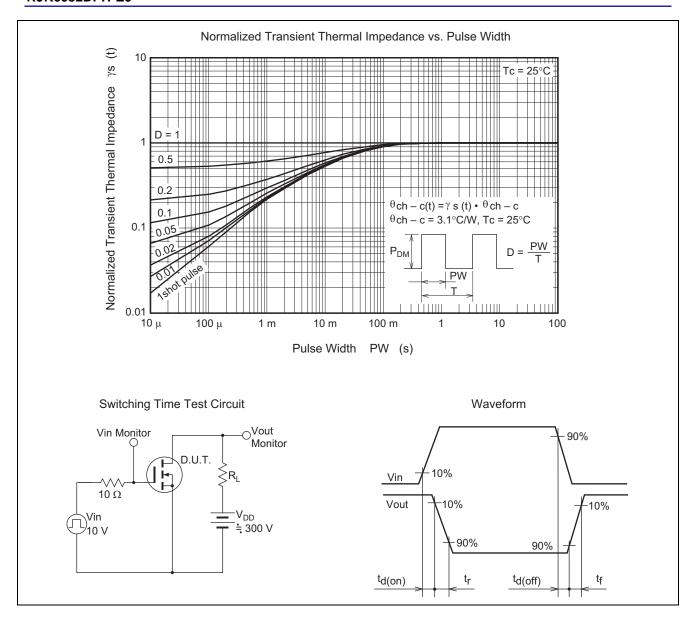
- 5. Since this device is equipped with high voltage FET chip ($V_{DSS} \ge 600 \text{ V}$), high voltage may be supplied. Therefore, please be sure to confirm about Electric discharge between Drain terminal and other terminal.
- 6. This device is sensitive to electrostatic discharge.

 It is recommended to adopt appropriate cautions when handling this product.

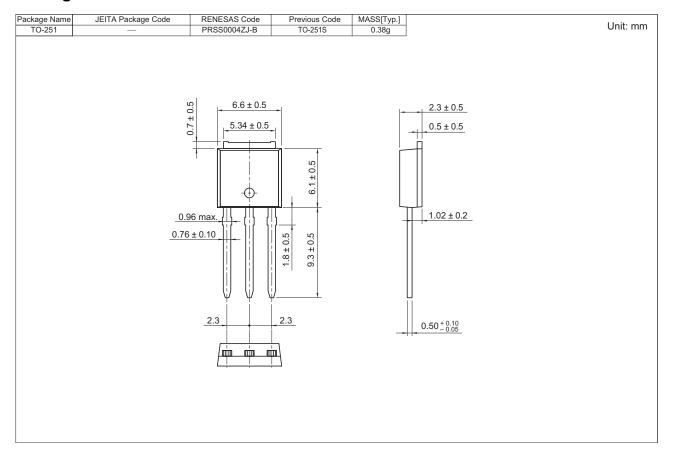
Main Characteristics







Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
RJK6032DPH-E0#T2	70 pcs	Tube

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